Bassem Salem

List of Publications by Year in descending order

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139	1,667	361296	395590
papers	citations	20 h-index	33 g-index

141	141	141	1606
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Tuneable polarity and enhanced piezoelectric response of ZnO thin films grown by metalâ€“organic chemical vapour deposition through the flow rate adjustment. Materials Advances, 2022, 3, 498-513.	2.6	5
2	H3PO4-based wet chemical etching for recovery of dry-etched GaN surfaces. Applied Surface Science, 2022, 582, 152309.	3.1	13
3	Functional Devices from Bottom-Up Silicon Nanowires: A Review. Nanomaterials, 2022, 12, 1043.	1.9	16
4	Implementing the Reactor Geometry in the Modeling of Chemical Bath Deposition of ZnO Nanowires. Nanomaterials, 2022, 12, 1069.	1.9	7
5	Enhancing the incorporation of Sn in vaporâ€“liquidâ€“solid GeSn nanowires by modulation of the droplet composition. Nanotechnology, 2022, 33, 245605.	1.3	0
6	Impact of Substrate Biasing During AlN Growth by PEALD on Al ₂ O ₃ /AlN/GaN MOS Capacitors. Advanced Materials Interfaces, 2022, 9, 2101731.	1.9	2
7	Verifying the band gap narrowing in tensile strained Ge nanowires by electrical means. Nanotechnology, 2021, 32, 145711.	1.3	6
8	Chemical Bath Deposition of ZnO Nanowires Using Copper Nitrate as an Additive for Compensating Doping. Inorganic Chemistry, 2021, 60, 1612-1623.	1.9	19
9	Smooth plasma etching of GeSn nanowires for gate-all-around field effect transistors. Semiconductor Science and Technology, 2021, 36, 065018.	1.0	4
10	Effects of thermal annealing on the structural and electrical properties of ZnO thin films for boosting their piezoelectric response. Journal of Alloys and Compounds, 2021, 870, 159512.	2.8	21
11	Monolithically integrated InGaAs/AlGaAs multiple quantum well photodetectors on 300Âmm Si wafers. AIP Advances, 2021, 11, .	0.6	5
12	Study of structural and electrical properties of ferroelectric HZO films obtained by single-target sputtering. AIP Advances, 2021, 11, .	0.6	6
13	Development of a robust fabrication process for single silicon nanowire-based omega gate transistors on polyamide substrate. Semiconductor Science and Technology, 2021, 36, 025003.	1.0	3
14	A fabrication process for self-connected horizontal SiGe nanowires. Microelectronic Engineering, 2020, 220, 111150.	1.1	1
15	Analysis of the role of inter-nanowire junctions on current percolation effects in silicon nanonet field-effect transistors. Solid-State Electronics, 2020, 168, 107725.	0.8	4
16	Role played by the nanowire/nanowire junctions in the electrical properties of semiconductor percolating silicon nanowire networks. Journal of Applied Physics, 2020, 128, 204501.	1.1	1
17	Improvement of AlN Film Quality Using Plasma Enhanced Atomic Layer Deposition with Substrate Biasing. ACS Applied Materials & Interfaces, 2020, 12, 39870-39880.	4.0	20
18	Optimization of GOPS-Based Functionalization Process and Impact of Aptamer Grafting on the Si Nanonet FET Electrical Properties as First Steps towards Thrombin Electrical Detection. Nanomaterials, 2020, 10, 1842.	1.9	4

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19	O-Band Emitting InAs Quantum Dots Grown by MOCVD on a 300 mm Ge-Buffered Si (001) Substrate. Nanomaterials, 2020, 10, 2450.	1.9	5
20	Reversible Al Propagation in Si_xGe_{1â€“x} Nanowires: Implications for Electrical Contact Formation. ACS Applied Nano Materials, 2020, 3, 10427-10436.	2.4	4
21	Morphology Transition of ZnO from Thin Film to Nanowires on Silicon and its Correlated Enhanced Zinc Polarity Uniformity and Piezoelectric Responses. ACS Applied Materials & Interfaces, 2020, 12, 29583-29593.	4.0	11
22	Impact of droplet composition on the nucleation rate and morphology of vapor-liquid-solid GeSn nanowires. Nanotechnology, 2020, 31, 405602.	1.3	5
23	Material engineering of percolating silicon nanowire networks for reliable and efficient electronic devices. Materials Chemistry and Physics, 2019, 238, 121871.	2.0	12
24	Improvement of the electrical performance of Au/Ti/HfO2/Ge0.9Sn0.1 p-MOS capacitors by using interfacial layers. Applied Physics Letters, 2019, 115, 171601.	1.5	4
25	Modeling the Elongation of Nanowires Grown by Chemical Bath Deposition Using a Predictive Approach. Journal of Physical Chemistry C, 2019, 123, 29476-29483.	1.5	18
26	Impact of Wet Treatments on the Electrical Performance of Ge_{0.9}Sn_{0.1}-Based p-MOS Capacitors. ACS Applied Electronic Materials, 2019, 1, 260-268.	2.0	8
27	Linear and Nonlinear Intersubband Optical Properties of Direct Band Gap GeSn Quantum Dots. Nanomaterials, 2019, 9, 124.	1.9	16
28	Intersubband Optical Nonlinearity of GeSn Quantum Dots under Vertical Electric Field. Micromachines, 2019, 10, 243.	1.4	5
29	Monolithic fabrication of nano-to-millimeter scale integrated transistors based on transparent and flexible silicon nanonets. Nano Futures, 2019, 3, 025002.	1.0	5
30	Formation mechanisms of ZnO nanowires on polycrystalline Au seed layers for piezoelectric applications. Nanotechnology, 2019, 30, 345601.	1.3	10
31	Engineering Self-Assembly of a High-Ï‡ Block Copolymer for Large-Area Fabrication of Transistors Based on Functional Graphene Nanoribbon Arrays. Chemistry of Materials, 2019, 31, 3154-3162.	3.2	12
32	Investigation of GeSn/Ge quantum dotsâ€™ optical transitions for integrated optics on Si substrate. Results in Physics, 2019, 12, 1732-1736.	2.0	6
33	InAs/GaSb thin layers directly grown on nominal (0â€¯0â€¯1)-Si substrate by MOVPE for the fabrication of InAs FINFET. Journal of Crystal Growth, 2019, 510, 18-22.	0.7	3
34	First evidence of superiority of Si nanonet field effect transistors over multi-parallel Si nanowire ones in view of electrical DNA hybridization detection. Materials Research Express, 2019, 6, 016301.	0.8	4
35	Tuning direct bandgap GeSn/Ge quantum dots' interband and intraband useful emission wavelength: Towards CMOS compatible infrared optical devices. Superlattices and Microstructures, 2018, 117, 31-35.	1.4	9
36	Growth of Ge_{1â^’x}Sn_x Nanowires by Chemical Vapor Deposition via Vaporâ€“Liquidâ€“Solid Mechanism Using GeH₄ and SnCl₄. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700743.	0.8	18

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37	Electrical characteristics of silicon percolating nanonet-based field effect transistors in the presence of dispersion. Solid-State Electronics, 2018, 143, 83-89.	0.8	5
38	An innovative large scale integration of silicon nanowire-based field effect transistors. Solid-State Electronics, 2018, 143, 97-102.	0.8	20
39	Direct measurement of AC electrokinetics properties and capture frequencies of silicon and siliconâ€“germanium nanowires. Semiconductor Science and Technology, 2018, 33, 015005.	1.0	1
40	Design of Strain-Engineered GeSn/GeSiSn Quantum Dots for Mid-IR Direct Bandgap Emission on Si Substrate. Nanoscale Research Letters, 2018, 13, 172.	3.1	9
41	Understanding and improving the low optical emission of InGaAs quantum wells grown on oxidized patterned (001) silicon substrate. Applied Physics Letters, 2018, 112, .	1.5	2
42	Evaluation of Silicon Nanonet Field Effect Transistor as Photodiodes. Proceedings (mdpi), 2018, 2, 124.	0.2	0
43	Fabrication of top-down gold nanostructures using a damascene process. Microelectronic Engineering, 2017, 177, 41-45.	1.1	6
44	Impact of the wetting layer thickness on the emission wavelength of direct band gap GeSn/Ge quantum dots. Materials Research Express, 2017, 4, 075026.	0.8	3
45	Sub-10â€‰nm plasma nanopatterning of InGaAs with nearly vertical and smooth sidewalls for advanced n-fin field effect transistors on silicon. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, 021206.	0.6	2
46	Toward the integration of Si nanonets into FETs for biosensing applications. , 2017, , .		3
47	Electrical characterization of percolating silicon nanonet FETs for sensing applications. , 2017, , .		2
48	Fabrication and characterization of a germanium nanowire light emitting diode. Applied Physics Letters, 2017, 111, 233103.	1.5	2
49	Impact of laser anneal on NiPt silicide texture and chemical composition. Journal of Applied Physics, 2017, 121, .	1.1	6
50	On the Development of Label-Free DNA Sensor Using Silicon Nanonet Field-Effect Transistors. Proceedings (mdpi), 2017, 1, .	0.2	4
51	Fabrication and electrical characterization of homo- and hetero-structure Si/SiGe nanowire Tunnel Field Effect Transistor grown by vaporâ€“liquidâ€“solid mechanism. Solid-State Electronics, 2016, 118, 26-29.	0.8	17
52	Thermally activated inter-dots carriers' transfer in InAs QDs with InGaAs underlying layer: Origin and dependence on the post-growth intermixing. Journal of Alloys and Compounds, 2016, 656, 132-137.	2.8	11
53	Fabrication and characterization of silicon nanowire p-i-n MOS gated diode for use as p-type tunnel FET. Applied Physics A: Materials Science and Processing, 2015, 121, 1285-1290.	1.1	13
54	Functionalized silicon nanowires/conjugated polymer hybrid solar cells: Optical, electrical and morphological characterizations. Journal of Luminescence, 2015, 168, 315-324.	1.5	14

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55	Integration of SiC-1D nanostructures into nano-field effect transistors. Materials Science in Semiconductor Processing, 2015, 29, 218-222.	1.9	20
56	Dopant profiling in silicon nanowires measured by scanning capacitance microscopy. Physica Status Solidi - Rapid Research Letters, 2014, 8, 312-316.	1.2	11
57	High density and taper-free boron doped Si1âˆ’xGex nanowire via two-step growth process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 041401.	0.9	1
58	Growth strategies to control tapering in Ge nanowires. APL Materials, 2014, 2, .	2.2	16
59	Interfacial abruptness in axial Si/SiGe heterostructures in nanowires probed by scanning capacitance microscopy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 509-513.	0.8	6
60	Control of heterointerface and strain mapping in Au catalyzed axial Si-Si1-xGex nanowires. Materials Research Society Symposia Proceedings, 2014, 1707, 37.	0.1	0
61	Carriers' localization and thermal redistribution in post growth voluntarily tuned quantum dashes' size/composition distribution. Journal of Luminescence, 2014, 145, 595-599.	1.5	7
62	Impact of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-type doping on the carrier dynamics of silicon nanowires studied using optical-pump terahertz-probe spectroscopy. Physical Review B, 2014, 89, .	1.1	14
63	Control of the interfacial abruptness of Au-catalyzed Si-Si1âˆ’xGex heterostructured nanowires grown by vaporâ€“liquidâ€“solid. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	0.9	4
64	Composition-Dependent Interfacial Abruptness in Au-Catalyzed Si_{1â€“x}Ge_x/Si/Si_{1â€“x}Ge_x Nanowire Heterostructures. Nano Letters, 2014, 14, 5140-5147.	4.5	34
65	Hybrid nanocomposites based on conducting polymer and silicon nanowires for photovoltaic application. Journal of Luminescence, 2014, 156, 30-35.	1.5	11
66	Postgrowth intermixing of strain engineered InAs/GaAs quantum dots. Journal of Alloys and Compounds, 2014, 615, 683-686.	2.8	6
67	Distribution of barrier heights in metal/n-InAlAs Schottky diodes from currentâ€“voltageâ€“temperature measurements. Materials Science in Semiconductor Processing, 2014, 26, 431-437.	1.9	37
68	Electrical characterisation of horizontal and vertical gate-all-around Si/SiGe nanowires field effect transistors. , 2014, , .		0
69	Effect of HCl on the doping and shape control of silicon nanowires. Nanotechnology, 2012, 23, 215702.	1.3	64
70	Fabrication of SiC Nanopillars by Inductively Coupled SF₆/O₂ Plasma. Materials Science Forum, 2012, 711, 66-69.	0.3	2
71	ELECTRICAL CHARACTERIZATION OF PLANAR SILICON NANOWIRE FIELD-EFFECT TRANSISTORS. International Journal of Nanoscience, 2012, 11, 1240011.	0.4	0
72	Composition and Size Effects on the Optical Properties of Isolated Silicon-Germanium Nanowires. Materials Research Society Symposia Proceedings, 2012, 1408, 3.	0.1	0

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73	From planar to vertical nanowires field-effect transistors. Materials Research Society Symposia Proceedings, 2012, 1439, 101-107.	0.1	0
74	PiezoNEMS: Semiconductor nanowires and heterostructures for sensing and energy harvesting. , 2012, , .		1
75	Tunable enhancement of light absorption and scattering in Si<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Ge<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>nanowires. Physical Review B, 2012, 86, .		22
76	Geometrical control of photocurrent in active Si nanowire devices. Nano Energy, 2012, 1, 714-722.	8.2	15
77	High-performance silicon nanowire field-effect transistor with silicided contacts. Semiconductor Science and Technology, 2011, 26, 085020.	1.0	40
78	Quantum confinement effects and strain-induced band-gap energy shifts in core-shell Si-SiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>nanowires. Physical Review B, 2011, 83, .	1.1	17
79	Coulomb charging effect of electrons in InAs/InAlAs quantum dots studied by capacitance techniques. Physica B: Condensed Matter, 2011, 406, 3531-3533.	1.3	4
80	Temperature Dependent Photoluminescence Properties of InAs/InP Quantum Dashes Subjected to Low Energy Phosphorous Ion Implantation and Subsequent Annealing. Journal of Nanoscience and Nanotechnology, 2011, 11, 9251-9255.	0.9	3
81	Controlled growth of SiGe nanowires by addition of HCl in the gas phase. Journal of Applied Physics, 2011, 110, 024311.	1.1	26
82	Electrical characteristics of a vertically integrated field-effect transistor using non-intentionally doped Si nanowires. Microelectronic Engineering, 2011, 88, 3312-3315.	1.1	17
83	From Si nanowire to SiC nanotube. Journal of Nanoparticle Research, 2011, 13, 5425-5433.	0.8	23
84	Tunnelling current in Schottky diodes containing InAs quantum dots. Superlattices and Microstructures, 2011, 50, 164-172.	1.4	2
85	Growth and characterization of gold catalyzed SiGe nanowires and alternative metal-catalyzed Si nanowires. Nanoscale Research Letters, 2011, 6, 187.	3.1	19
86	Study of CVD nanowire high-k metal interface quality for interconnect level MOS devices. Microelectronic Engineering, 2011, 88, 1228-1231.	1.1	0
87	Wideband frequency and in situ characterization of aluminum nitride (AlN) in a metal/insulator/metal (MIM) configuration. Microelectronic Engineering, 2011, 88, 564-568.	1.1	1
88	Patterned growth of high aspect ratio silicon wire arrays at moderate temperature. Journal of Crystal Growth, 2011, 321, 151-156.	0.7	10
89	InGaAs Quantum Dots Grown by Molecular Beam Epitaxy for Light Emission on Si Substrates. Journal of Nanoscience and Nanotechnology, 2011, 11, 9153-9159.	0.9	4
90	Vertically integrated silicon-germanium nanowire field-effect transistor. Applied Physics Letters, 2011, 99, 193107.	1.5	23

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91	An improved AFM cross-sectional method for piezoelectric nanostructures properties investigation: application to GaN nanowires. Nanotechnology, 2011, 22, 105704.	1.3	33
92	Persistence of In/Ga intermixing beyond the emission energy blueshift saturation of proton-implanted InAs/GaAs quantum dots. Journal of Applied Physics, 2010, 107, .	1.1	1
93	Silicon nanowires: Diameter dependence of growth rate and delay in growth. Applied Physics Letters, 2010, 96, .	1.5	64
94	Impact of ion-implantation-induced band gap engineering on the temperature-dependent photoluminescence properties of InAs/InP quantum dashes. Journal of Applied Physics, 2010, 108, 024317.	1.1	4
95	Surface Recombination Velocity Measurements of Efficiently Passivated Gold-Catalyzed Silicon Nanowires by a New Optical Method. Nano Letters, 2010, 10, 2323-2329.	4.5	56
96	Electrical properties of self-assembled InAs/InAlAs quantum dots on InP. Semiconductor Science and Technology, 2010, 25, 065011.	1.0	3
97	Intermixing of InAs/GaAs quantum dots by proton implantation and rapid thermal annealing. Materials Science in Semiconductor Processing, 2009, 12, 71-74.	1.9	4
98	Self-connected horizontal silicon nanowire field effect transistor. Solid State Communications, 2009, 149, 799-801.	0.9	10
99	Chemical-vapour-deposition growth and electrical characterization of intrinsic silicon nanowires. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 83-86.	1.7	6
100	Optical investigation of phosphorous-ion-implantation induced InAs/GaAs quantum dots' intermixing. Physics Letters, Section A: General, Atomic and Solid State Physics, 2008, 372, 4714-4717.	0.9	1
101	Capacitanceâ€“voltage analysis of InAs quantum dots grown on InAlAs/InP(001). Microelectronics Journal, 2008, 39, 7-11.	1.1	6
102	Inhomogeneous broadening and alloy intermixing in low proton dose implanted InAs/GaAs self-assembled quantum dots. Nanotechnology, 2008, 19, 285715.	1.3	3
103	Effect of the Er-Si interatomic distance on the Er3+ luminescence in silicon-rich silicon oxide thin films. Journal of Applied Physics, 2007, 102, 103516.	1.1	6
104	Deep level transient spectroscopy studies at low temperature of In0.52Al0.48As epilayers. Physica B: Condensed Matter, 2007, 391, 18-21.	1.3	2
105	Terahertz emission properties of arsenic and oxygen ion-implanted GaAs based photoconductive pulsed sources. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 774-777.	0.9	22
106	Hole emission processes from InAs quantum dots grown on p-type InAlAs/InP(0â€‰0â€‰1). Semiconductor Science and Technology, 2006, 21, 311-315.	1.0	5
107	Optical transitions and carrier dynamics in self-organized InAs quantum dots grown on In0.52Al0.48As/InP(001). Physica E: Low-Dimensional Systems and Nanostructures, 2006, 31, 232-234.	1.3	1
108	Photoluminescence from Er-doped silicon rich oxide thin films. Journal of Luminescence, 2006, 121, 242-244.	1.5	4

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109	Capacitanceâ€“voltage profile characteristics of Schottky barrier structure with InAs quantum dots grown on InAlAs/InP(001). Materials Science and Engineering C, 2006, 26, 583-585.	3.8	1
110	Optimizing the spacer layer thickness of vertically stacked InAs/GaAs quantum dots. Materials Science and Engineering C, 2006, 26, 374-377.	3.8	22
111	Post-growth engineering of InAs/GaAs quantum dotsâ€™ band-gap using proton implantation and annealing. Nanotechnology, 2006, 17, 3707-3709.	1.3	20
112	Improved characteristics of a terahertz set-up built with an emitter and a detector made on proton-bombarded GaAs photoconductive materials. Semiconductor Science and Technology, 2006, 21, 283-286.	1.0	27
113	Size and shape effects on excitons and biexcitons in single InAsâˆ•InP quantum dots. Journal of Applied Physics, 2006, 100, 073702.	1.1	18
114	Photoluminescence studies of stacked InAs/InP quantum sticks. Journal of Crystal Growth, 2005, 275, e2327-e2331.	0.7	4
115	Micro-photoluminescence study of single self-organized InAs/InP quantum sticks. Materials Science and Engineering C, 2005, 25, 650-653.	3.8	0
116	Optical properties of 1.3ÂÎ¼m room temperature emitting InAs quantum dots covered by In0.4Ga0.6As/GaAs hetero-capping layer. Applied Physics A: Materials Science and Processing, 2005, 81, 813-816.	1.1	17
117	Arsenic pressure and spacer layer thickness effects on the optical properties of stacked InAs/InAlAs quantum dot array. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1399-1403.	0.8	2
118	High-performance terahertz source using ion implanted photoconductive antenna. , 2005, , .		3
119	Pulsed photoconductive antenna terahertz sources made on ion-implanted GaAs substrates. Journal of Physics Condensed Matter, 2005, 17, 7327-7333.	0.7	39
120	Band gap tuning of InAsâˆ•InP quantum sticks using low-energy ion-implantation-induced intermixing. Applied Physics Letters, 2005, 87, 241115.	1.5	18
121	Ion channeling effects on quantum well intermixing in phosphorus-implanted InGaAsPâˆ•InGaAsâˆ•InP. Journal of Applied Physics, 2005, 98, 054904.	1.1	6
122	Optical transitions and carrier dynamics in self-organized InAs quantum islands grown on InP(001). , 2005, 5734, 27.		0
123	Optical investigation of single self-organized InAs/InP quantum dashes emitting in the 1.3â€“1.5 Âµm range. Nanotechnology, 2005, 16, 444-447.	1.3	5
124	Effective generation lifetime depth profile in InAs quantum dots grown on InAlAs/InP(0â€‰0â€‰1). Semiconductor Science and Technology, 2005, 20, 514-518.	1.0	7
125	From large to low height dispersion for self-organized InAs quantum sticks emitting at 1.55 Î¼m on InP (001). Journal of Applied Physics, 2004, 95, 4761-4766.	1.1	79
126	Experimental and theoretical investigation of carrier confinement in InAs quantum dashes grown on InP(001). Journal of Applied Physics, 2004, 95, 1074-1080.	1.1	52

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127	Effect of spacer layer thickness on the optical properties of stacked InAs/InAlAs quantum wires grown on InP (001). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 259-261.	1.7	6
128	Evidence of excited levels in self-organized InAs/InP(001) islands with low size dispersion. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 124-126.	1.3	9
129	Optical properties of self-organized InAs nanostructures grown on InAlAs/InP(001). Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 180-182.	1.3	7
130	Anti-correlated vertical self-organization of InAs nanowires in stacked structures on InP(001) with InAlAs spacer layer. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 505-506.	1.3	5
131	Spacer layer thickness effects on the photoluminescence properties of InAs/GaAs quantum dot superlattices. Physica Status Solidi A, 2003, 199, 457-463.	1.7	21
132	Dynamic saturation of an intersublevel transition in self-organizedInAs/InxAl1â^'xAsquantum dots. Physical Review B, 2003, 67, .	1.1	11
133	Optical properties of self-assembled InAs quantum dots grown on InAlAs/InP(001). Materials Research Society Symposia Proceedings, 2002, 737, 254.	0.1	1
134	Surface effects on shape, self-organization and photoluminescence of InAs islands grown on InAlAs/InP(001). Journal of Applied Physics, 2002, 92, 506-510.	1.1	98
135	Strong carrier confinement and evidence for excited states in self-assembled InAs quantum islands grown on InP(001). Physical Review B, 2002, 66, .	1.1	35
136	Optical anisotropy and photoluminescence temperature dependence for self-assembled InAs quantum islands grown on vicinal (001) InP substrates. Microelectronics Journal, 2002, 33, 579-582.	1.1	5
137	Optical properties of self-assembled InAs quantum islands grown on InP(001) vicinal substrates. Applied Physics Letters, 2001, 79, 4435-4437.	1.5	38
138	Chemical Stability of Si-SiC Nanostructures under Physiological Conditions. Materials Science Forum, 0, 897, 638-641.	0.3	8
139	Influence of substrate biasing on structural, chemical and electrical properties of Al₂O₃ thin films deposited by PEALD. Semiconductor Science and Technology, 0, , .	1.0	0